

N-CHANNEL MOS FIELD EFFECT POWER TRANSISTOR

**Phase-out/Discontinued** **2SK926**

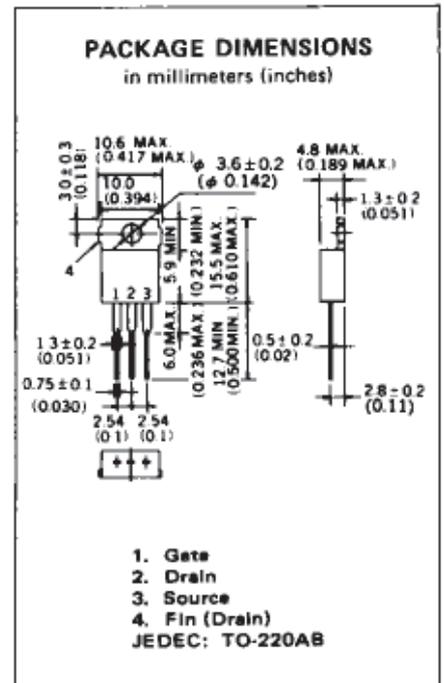
**DESCRIPTION** The 2SK926 is N-channel MOS Field Effect Power Transistor designed for switching power supplies, DC-DC converters.

- FEATURES**
- Suitable for switching power supplies, actuator controls, and pulse circuits.
  - Low  $R_{DS(on)}$
  - No second breakdown

**ABSOLUTE MAXIMUM RATINGS**

- Maximum Temperatures**
- Storage Temperature . . . . . -55 to +150 °C
  - Channel Temperature . . . . . 150 °C Maximum
- Maximum Power Dissipation ( $T_C = 25\text{ °C}$ )**
- Total Power Dissipation . . . . . 60 W
- Maximum Voltages and Currents ( $T_a = 25\text{ °C}$ )**
- $V_{DSS}$  Drain to Source Voltage . . . . . 250 V
  - $V_{GSS}$  Gate to Source Voltage . . . . .  $\pm 20$  V
  - $I_D(DC)$  Drain Current (DC) . . . . .  $\pm 10$  A
  - $I_D(pulse)$  Drain Current (pulse)\* . . . . .  $\pm 40$  A

\* PW  $\leq 10\ \mu s$ , Duty Cycle  $\leq 1\%$



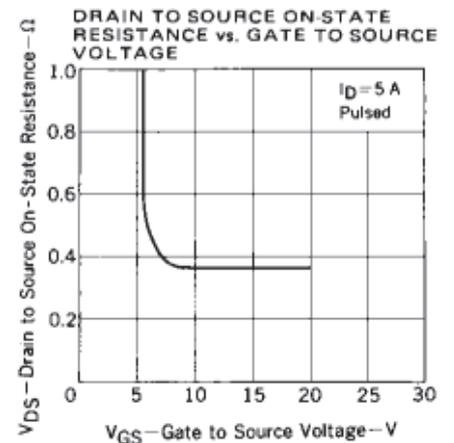
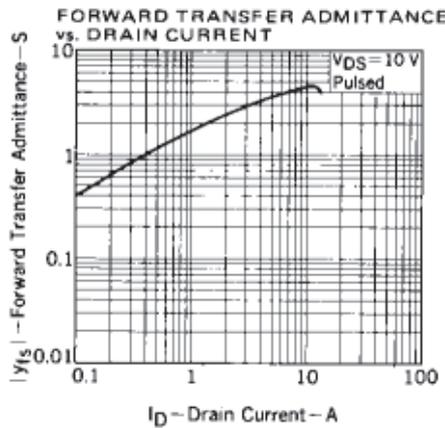
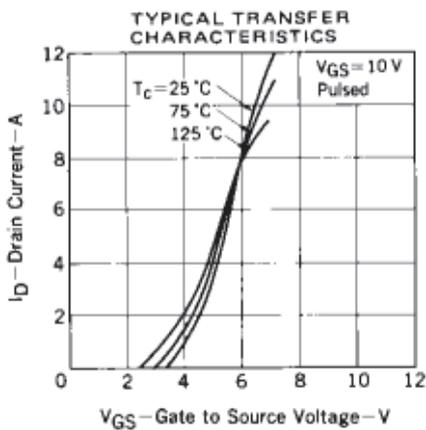
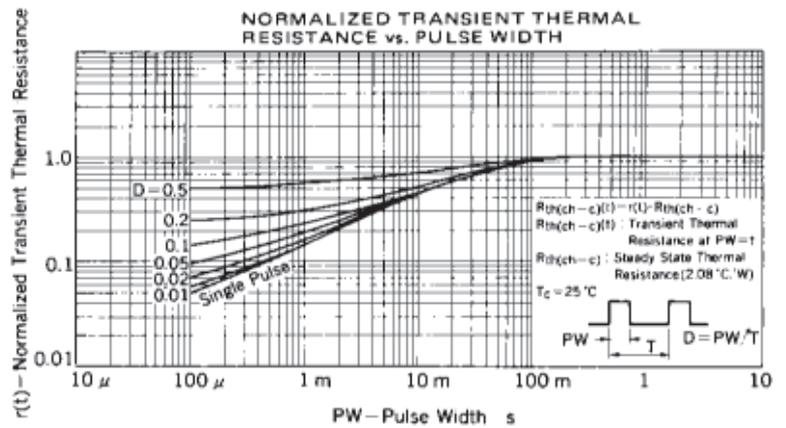
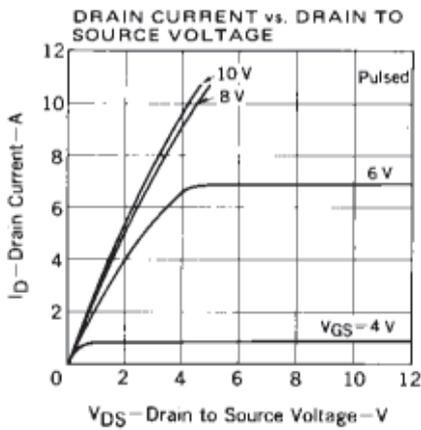
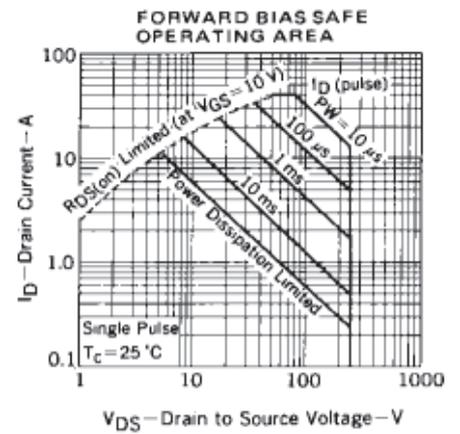
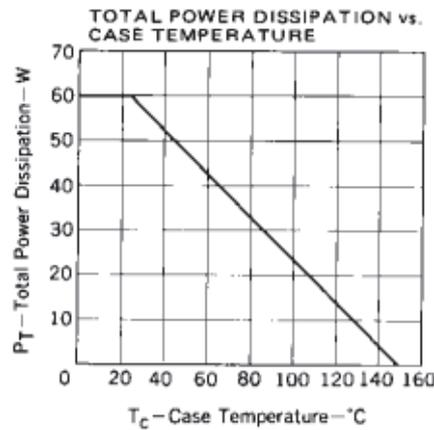
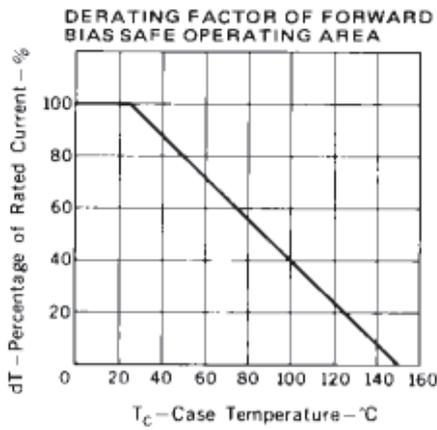
**ELECTRICAL CHARACTERISTICS ( $T_a = 25\text{ °C}$ )**

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
$I_{DSS}$	Drain Leakage Current			100	$\mu A$	$V_{DS} = 250\text{ V}, V_{GS} = 0$
$I_{GSS}$	Gate to Source Leakage Current			$\pm 100$	nA	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	1.5		3.5	V	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$
$ Y_{fs} $	Forward Transfer Admittance	2.5			S	$V_{DS} = 10\text{ V}, I_D = 5\text{ A}$
$R_{DS(on)}$	Drain to Source On-State Resistance			0.5	$\Omega$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$
$C_{iss}$	Input Capacitance		940		pF	$V_{DS} = 10\text{ V},$ $V_{GS} = 0,$ $f = 1\text{ MHz}$
$C_{oss}$	Output Capacitance		340		pF	
$C_{rss}$	Reverse Transfer Capacitance		100		pF	
$t_{d(on)}$	Turn-On Delay Time		20		ns	$I_D = 5\text{ A}, V_{DD} \cong 150\text{ V}$ $V_{GS(on)} = 10\text{ V}$ $R_L = 30\ \Omega$ $R_{in} = 10\ \Omega$
$t_r$	Rise Time		30		ns	
$t_{d(off)}$	Turn-Off Delay Time		60		ns	
$t_f$	Fall Time		20		ns	

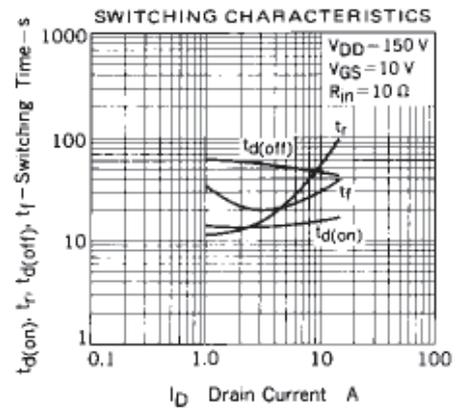
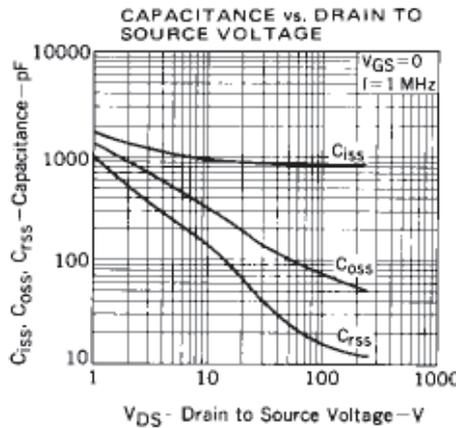
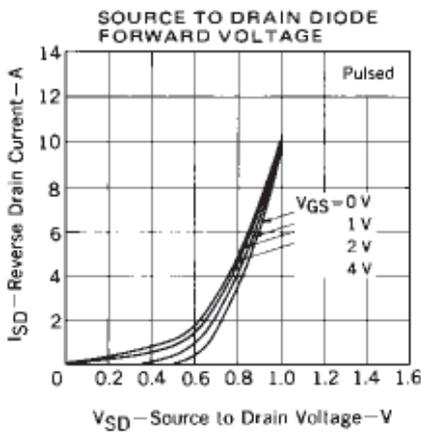
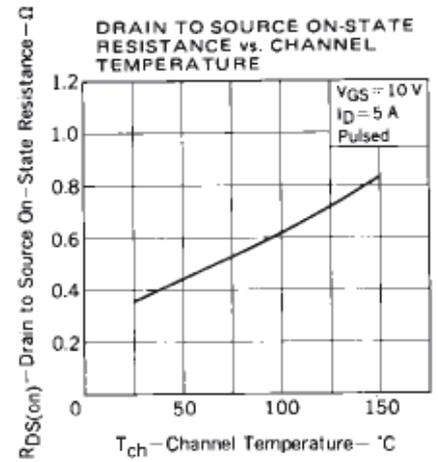
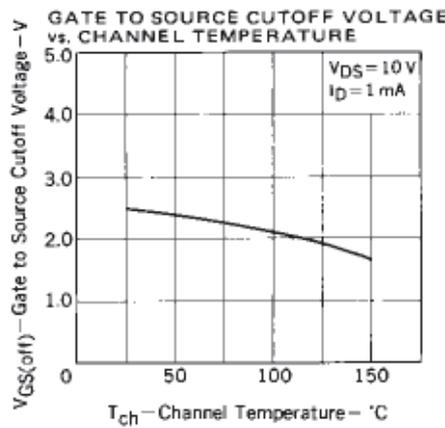
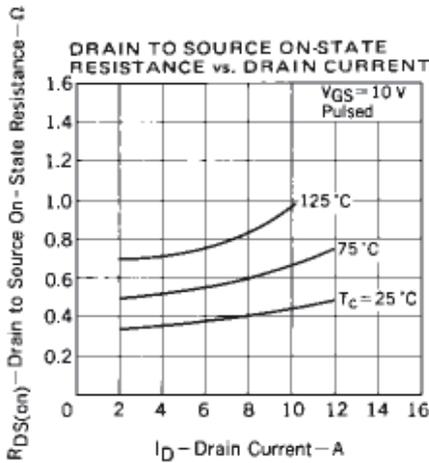
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**Phase-out/Discontinued**

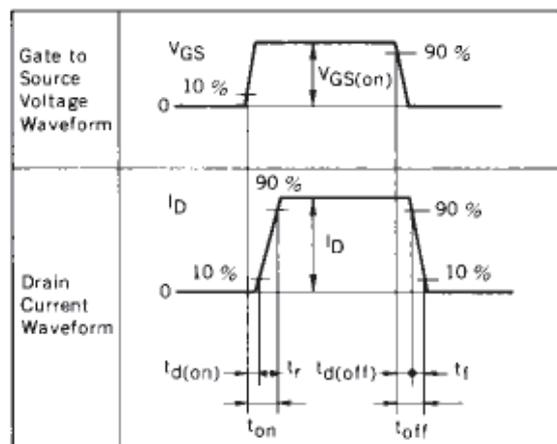
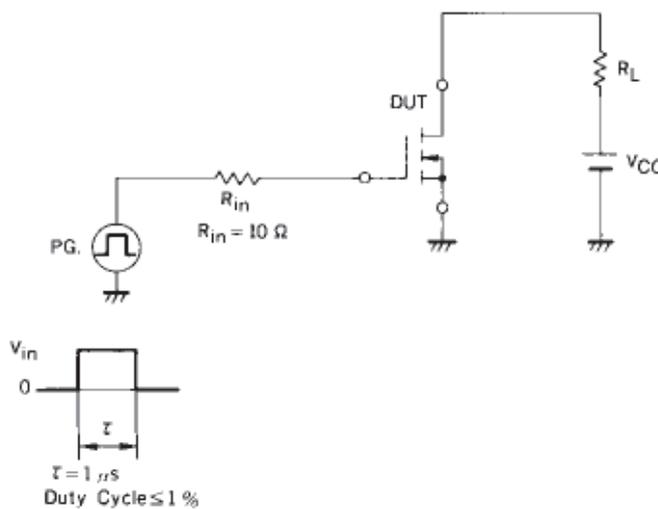
TYPICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )



**Phase-out/Discontinued**



**SWITCHING TIME TEST CIRCUIT**



**Phase-out/Discontinued**